

AMENDMENTS TO THE SPECIFICATION

By the instant amendment, the specification is amended to correct a typographical error. In the following amendments to the specification, references to paragraph numbers are made with respect to the published application, 2004/0235260 A1 and, parenthetically, to the application as filed on April 23, 2004. Please amend the specification as follows.

Please replace paragraph [0018] ([0016] in the application as filed) of the specification with the paragraph below, which is marked-up to show the changes therein:

[0018] Next, the resultant structure is planarized by CMP until the second ILD 46 is exposed, and the second ILD 46 is etched by a HF [[Hf]] wet etch process to form a stack-type lower electrode 41 (refer to FIG. 3D).

Also, please replace paragraph [0055] ([0053] in the application as filed) of the specification with the paragraph below, which is marked-up to show the changes therein:

[0055] Next, the Ru layer 141a and the TiAlN layer 141b are planarized by CMP until the insulating layer 146 is exposed. The second ILD 146 is etched using a HF [[Hf]] wet etch process, thereby forming a stack-type lower electrode 141 as shown in FIG. 8E.